



**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (original): A p-type semiconductor material expressed in a composition formula of  $\text{Zn}_{(1-\alpha-\beta-\gamma)}\text{Cu}_\alpha\text{A}_\beta\text{B}_\gamma\text{S}_{(1-x-y)}\text{Se}_x\text{Te}_y$  ( $0.004 \leq \alpha \leq 0.4$ ,  $\beta \leq 0.2$ ,  $\gamma \leq 0.2$ ,  $0 \leq x \leq 1$ ,  $0 \leq y \leq 0.2$ , and  $x + y \leq 1$ , A and B are elements selected from Cd, Hg and alkaline earth metals).
2. (original): The p-type semiconductor material according to claim 1, wherein the A is Mg.
3. (original): The p-type semiconductor material according to claim 1, wherein the B is Cd.
4. (original): The p-type semiconductor material according to claim 2, wherein the B is Cd.
5. (previously presented): The p-type semiconductor material according to claim 1, wherein the semiconductor material contains at least one dopant selected from Cl, Br, I, Al, Ga and In as a compensation dopant and a concentration of the compensation dopant is  $10^{17}$  to  $10^{20} \text{ cm}^{-3}$ .
6. (previously presented): The p-type semiconductor material according to claim 1, wherein the semiconductor material has a light absorption coefficient of  $5 \times 10^5 \text{ cm}^{-1}$  or less at 470 nm to 750 nm.

7. (currently amended): The p-type semiconductor material according to claim 1, wherein a volume resistivity of the semiconductor material is equal to or higher than  $10^{-4}\Omega\text{cm}$  and is lower than  ~~$10^{-3}\Omega\text{cm}$~~   $10^3\Omega\text{cm}$ .

8. (previously presented): The p-type semiconductor material according to claim 1, wherein a carrier concentration of the semiconductor material is equal to or higher than  $10^{16}\text{ cm}^{-3}$  and is lower than  $10^{22}\text{ cm}^{-3}$ .

9. (previously presented): A semiconductor device in which the p-type semiconductor material according to claim 1, constitutes a hole injecting electrode layer in an amorphous phase or a polycrystalline phase.

10. (original): The semiconductor device according to claim 9, wherein the semiconductor device is a light emitting device.

11. (previously presented): The p-type semiconductor material according to claim 2, wherein the semiconductor material contains at least one dopant selected from Cl, Br, I, Al, Ga and In as a compensation dopant and a concentration of the compensation dopant is  $10^{17}$  to  $10^{20}\text{ cm}^{-3}$ .

12. (previously presented): The p-type semiconductor material according to claim 3, wherein the semiconductor material contains at least one dopant selected from Cl, Br, I, Al, Ga and In as a compensation dopant and a concentration of the compensation dopant is  $10^{17}$  to  $10^{20}\text{ cm}^{-3}$ .

13. (previously presented): The p-type semiconductor material according to claim 4, wherein the semiconductor material contains at least one dopant selected from Cl, Br, I, Al, Ga

and In as a compensation dopant and a concentration of the compensation dopant is  $10^{17}$  to  $10^{20}$   $\text{cm}^{-3}$ .

14. (previously presented): The p-type semiconductor material according to claim 2, wherein the semiconductor material has a light absorption coefficient of  $5 \times 10^5 \text{ cm}^{-1}$  or less at 470 nm to 750 nm.

15. (previously presented): The p-type semiconductor material according to claim 3, wherein the semiconductor material has a light absorption coefficient of  $5 \times 10^5 \text{ cm}^{-1}$  or less at 470 nm to 750 nm.

16. (previously presented): The p-type semiconductor material according to claim 4, wherein the semiconductor material has a light absorption coefficient of  $5 \times 10^5 \text{ cm}^{-1}$  or less at 470 nm to 750 nm.

17. (currently amended): The p-type semiconductor material according to claim 2, wherein a volume resistivity of the semiconductor material is equal to or higher than  $10^{-4} \Omega\text{cm}$  and is lower than  ~~$10^{-3} \Omega\text{cm}$~~   $10^3 \Omega\text{cm}$ .

18. (currently amended): The p-type semiconductor material according to claim 3, wherein a volume resistivity of the semiconductor material is equal to or higher than  $10^{-4} \Omega\text{cm}$  and is lower than  ~~$10^{-3} \Omega\text{cm}$~~   $10^3 \Omega\text{cm}$ .

19. (currently amended): The p-type semiconductor material according to claim 4, wherein a volume resistivity of the semiconductor material is equal to or higher than  $10^{-4} \Omega\text{cm}$  and is lower than  ~~$10^{-3} \Omega\text{cm}$~~   $10^3 \Omega\text{cm}$ .

20. (previously presented): The p-type semiconductor material according to claim 2, wherein a carrier concentration of the semiconductor material is equal to or higher than  $10^{16} \text{ cm}^{-3}$  and is lower than  $10^{22} \text{ cm}^{-3}$ .

21. (previously presented): The p-type semiconductor material according to claim 3, wherein a carrier concentration of the semiconductor material is equal to or higher than  $10^{16} \text{ cm}^{-3}$  and is lower than  $10^{22} \text{ cm}^{-3}$ .

22. (previously presented): The p-type semiconductor material according to claim 4, wherein a carrier concentration of the semiconductor material is equal to or higher than  $10^{16} \text{ cm}^{-3}$  and is lower than  $10^{22} \text{ cm}^{-3}$ .

23. (previously presented): A semiconductor device in which the p-type semiconductor material according to claim 2, constitutes a hole injecting electrode layer in an amorphous phase or a polycrystalline phase.

24. (previously presented): A semiconductor device in which the p-type semiconductor material according to claim 3, constitutes a hole injecting electrode layer in an amorphous phase or a polycrystalline phase.

25. (previously presented): A semiconductor device in which the p-type semiconductor material according to claim 4, constitutes a hole injecting electrode layer in an amorphous phase or a polycrystalline phase.

26. (previously presented): The semiconductor device according to claim 23, wherein the semiconductor device is a light emitting device.

27. (previously presented): The semiconductor device according to claim 24, wherein the semiconductor device is a light emitting device.

28. (previously presented): The semiconductor device according to claim 25, wherein the semiconductor device is a light emitting device.